

HIGH SPEED 2K X 16 DUAL-PORT SRAM

IDT7133SA/LA IDT7143SA/LA

Features

- High-speed access
 - Military: 25/35/45/55/70/90ns (max.)
 - Industrial: 55ns (max.)
- Commercial: 20/25/35/45/55/70/90ns (max.)
- Low-power operation
 - IDT7133/43SA

Active: 1150mW (typ.)

Standby: 5mW (typ.)
– IDT7133/43LA

Active: 1050mW (typ.)

Standby: 1mW (typ.)

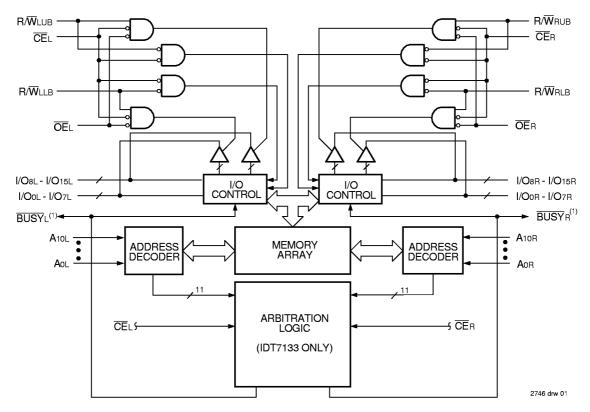
- Versatile control for write: separate write control for lower and upper byte of each port
- MASTER IDT7133 easily expands data bus width to 32 bits or more using SLAVE IDT7143
- On-chip port arbitration logic (IDT7133 only)

- ◆ BUSY output flag on IDT7133; BUSY input on IDT7143
- Fully asynchronous operation from either port
- Battery backup operation–2V data retention
- ◆ TTL-compatible; single 5V (±10%) power supply
- Available in 68-pin ceramic PGA, Flatpack, PLCC and 100-pin TQFP
- Military product compliant to MIL-PRF-38535 QML
- Industrial temperature range (-40°C to +85°C) is available for selected speeds

Description

The IDT7133/7143 are high-speed 2K x 16 Dual-Port Static RAMs. The IDT7133 is designed to be used as a stand-alone 16-bit Dual-Port RAM or as a "MASTER" Dual-Port RAM together with the IDT7143 "SLAVE" Dual-Port in 32-bit-or-more word width systems. Using the IDT MASTER/SLAVE Dual-Port RAM approach in 32-bit-or-wider

Functional Block Diagram



NOTE:

 IDT7133 (MASTER): BUSY is open drain output and requires pull-up resistor. IDT7143 (SLAVE): BUSY is input.

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memory system applications results in full-speed, error-free operation without the need for additional discrete logic.

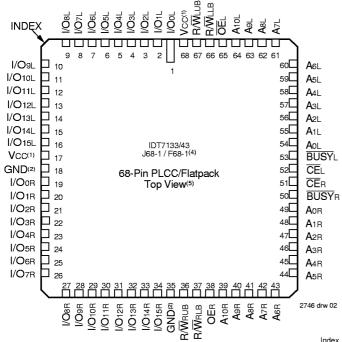
Both devices provide two independent ports with separate control, address, and I/O pins that permit independent, asynchronous access for reads or writes to any location in memory. An automatic power down feature, controlled by \overline{CE} , permits the on-chip circuitry of each port to enter a very low standby power mode.

Fabricated using IDT's CMOS high-performance technology, these devices typically operate on only 500mW of power. Low-power (LA)

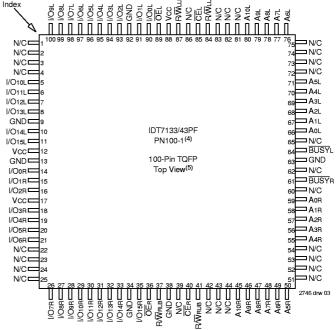
versions offer battery backup data retention capability, with each port typically consuming 200µW for a 2V battery.

The IDT7133/7143 devices have identical pinouts. Each is packed in a 68-pin ceramic PGA, 68-pin flatpack, 68-pin PLCC and 100-pin TQFP. Military grade product is manufactured in compliance with the latest revision of MIL-PRF-38535 QML, making it ideally suited to military temperature applications demanding the highest level of performance and reliability.

Pin Configurations (1,2,3)



- Both Vcc pins must be connected to the power supply to ensure reliable operation.
- Both GND pins must be connected to the ground supply to ensure reliable operation
- J68-Package body is approximately 0.95 in x 0.95 in x 0.17 in. F68-Package body is approximately 1.18 in x 1.18 in x 0.16 in. PN100-Package body is approximately 14mm x 14mm x 1.4mm.
- 4. This package code is used to reference the package diagram.
- 5. This text does not indicate orientation of the actual part-marking.



Pin Configurations^(1,2,3) (con't.)

11		51 A 6L	50 A 5L	48 А зL	46 A 1L	8USYL	42 CER	40 A or	38 A 2R	36 A 4R	
10	53 A 8L	52 A 7L	49 A 4L	47 A 2L	45 A 0L	43 CEL	41 BUSYR	39 A 1R	37 A 3R	35 A 5R	34 A 6R
09	55 A 10L	54 A 9L								32 A 8R	33 A 7R
08	57 R/WLLB	56 OEL								30 A 10R	31 A 9R
07	59 Vcc ⁽¹⁾	58 R/WLUB			ID ⁻		28 R/WRLB	29 ŌER			
06	61 I/O1L	60 I/OoL				26 GND(2)	27 R/ W RUB				
05	63 I/O3L	62 I/O2L				24 I/O14R	25 I/O15R				
04	65 I/O5L	64 I/O4L								22 I/O12R	23 I/O13R
03	67 I/O7L	66 I/O6L								20 I/O10R	21 I/O11R
02	68 I/O8L	1 I/O9L	3 I/O11L	5 I/O13L	7 I/O15L	9 GND ⁽²⁾	11 I/O1R	13 I/O3R	15 I/O5R	18 I/O8R	19 I/O9R
01	<u></u>	2 I/O10L	4 I/O12L	6 I/O14L	8 Vcc ⁽¹⁾	10 I/Oor	12 I/ O 2R	14 I/O4R	16 I/O6R	17 I/O 7R	
Pin 1' Designate	or A	В	С	D	E	F	G	Н	J	К	L

2746 drw 04

- 1. Both Vcc pins must be connected to the power supply to ensure reliable operation.
- 2. Both GND pins must be connected to the ground supply to ensure reliable operation.
- 3. Package body is approximately 1.18 in x 1.18 in x 0.16 in.
- 4. This package code is used to reference the package diagram.
 5. This text does not indicate orientation of the actual part-marking.

Pin Names

Left Port	Right Port	Names				
CEL	CER	Chip Enable				
R/WLUB	R/WRUB	Upper Byte Read/Write Enable				
R/WILB	R/WRLB	Lower Byte Read/Write Enable				
ŌĒL	ŌĒR	Output Enable				
A0L - A10L	A0R - A10R	Address				
VO0L - I/O15L	VO0R - VO15R	Data Input/Output				
BUSYL	BUSYR	Busy Flag				
Vcc		Power				
G	GND	Ground				

2746 tbl 01

Absolute Maximum Ratings(1)

Symbol	Rating	Commercial & Industrial	Military	Unit
VTERM ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +7.0	-0.5 to +7.0	>
TBIAS	Temperature Under Bias	-55 to +125	-65 to +135	°C
Tstg	Storage Temperature	-55 to +125	-65 to +150	°C
PT ⁽³⁾	Power Dissipation	2.0	2.0	W
ЮИТ	DC Output Current	50	50	mA

NOTES:

- Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may
 cause permanent damage to the device. This is a stress rating only and functional
 operation of the device at these or any other conditions above those indicated in
 the operational sections of this specification is not implied. Exposure to absolute
 maximum rating conditions for extended periods may affect reliability.
- 2. VTERM must not exceed Vcc + 10% for more than 25% of the cycle time or 10ns maximum, and is limited to ≤ 20mA for the period of VTERM ≥ Vcc + 10%.

Capacitance (TA = +25°C, f = 1.0mhz)

Symbol	Parameter ⁽¹⁾	Conditions ⁽²⁾	Max.	Unit
Cin	Input Capacitance	VIN = 3dV	11	pF
Соит	Output Capacitance	Vouτ = 3dV	11	pF

NOTES:

- This parameter is determined by device characterization but is not production tested.
- 3dV references the interpolated capacitance when the input and output switch from 0V to 3V or from 3V to 0V.

Maximum Operating Temperature and Supply Voltage^(1,2)

Grade	Ambient Temperature	GND	Vcc							
Military	-55°C to +125°C	0V	5.0V ± 10%							
Commercial	0°C to +70°C	0V	5.0V ± 10%							
Industrial	-40°C to +85°C	0V	5.0V <u>+</u> 10%							

NOTES

2746 tbl 02

2746 tbl 04

- 1. This is the parameter Ta.
- Industrial temperature: for specific speeds, packages and powers contact your sales office.

Recommended DC Operating Conditions

Symbol	Parameter	Min.	Тур.	Max.	Unit
Vcc	Supply Voltage	4.5	5.0	5.5	٧
GND	Ground	0	0	0	٧
Vih	Input High Voltage	2.2	_	6.0(2)	٧
VIL	Input Low Voltage	-0.5 ⁽¹⁾	_	0.8	٧

2746 tbl 05

NOTES:

- 1. VIL (min.) = -1.5V for pulse width less than 10ns.
- 2. VTERM must not exceed Vcc + 10%.

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range (Either port, Vcc = 5.0V ± 10%)

2746 tbl 03

			7133SA 7143SA		713 714		
Symbol	Parameter	Test Conditions	Min.	Max.	Min.	Max.	Unit
lu	Input Leakage Current ⁽¹⁾	Vcc = 5.5V, Vin = 0V to Vcc	_	10	1	5	μA
[LO]	Output Leakage Current	$\overline{\text{CE}}$ = ViH, Vout = 0V to Vcc	_	10	ı	5	μA
Vol	Output Low Voltage (I/Oo-I/O15)	IoL = 4mA	_	0.4	ı	0.4	٧
Vol	Open Drain Output Low Voltage (BUSY)	IoL = 16mA	_	0.5		0.5	٧
Vон	Output High Voltage	IOH = -4mA	2.4	_	2.4	_	٧

NOTE:

1. At Vcc ≤ 2.0V, input leakages are undefined.

2746 tbl 06

DC Electrical Characteristics Operating Temperature and Supply Voltage Range^(2,6) (Vcc = 5.0V ± 10%)

					7143	7133X20 7133X25 7133X35 7143X20 7143X25 7143X35 Com'l Only Com'l & Com'l & Military Military		X35 1 &			
Symbol	Parameter	Test Condition	Versi	on	Тур.(1)	Max.	Тур.(1)	Max.	Тур.(1)	Max.	Unit
lcc	Current (Both Ports Active) f = f(MAX ⁽³⁾	CE = VIL, Outputs Open	COM'L	\$ L	250 230	310 280	250 230	300 270	240 210	295 250	mA
		T = MAX ^e	MIL & IND	S L	_		250 230	330 300	240 220	325 295	
ISB1 Standby Current (Both Ports - TTL Level Inputs)	CEL and CER = VIH	COM'L	S L	25 25	80 70	25 25	80 70	25 25	70 60	mA	
	$f = f_{MAX}^{(3)}$	MIL & IND	S L	_	_	25 25	90 80	25 25	75 65		
ISB2	Standby Current (One Port - TTL	\overline{CE} "A" = VIL and \overline{CE} "B" = VIH ⁽⁴⁾ f=fMAX ⁽³⁾	COM'L	S L	140 120	200 180	140 100	200 170	120 100	180 160	mA
	Level Inputs)	Active Port Outputs Open	MIL &	S L	_		140 100	230 190	240 325 220 295 25 70 25 60 25 65 120 180 100 160 120 200 100 180 1.0 15 0.2 4		
ISB3	Full Standby Current (Both Ports -	Both Ports ŒL and ŒR > V∞ - 0.2V	COM'L	\$ L	1.0 0.2	15 5	1.0 0.2	15 4			mA
	CMOS Level Inputs)	VIN > VCC - 0.2V or VIN < 0.2V, f = 0 ⁽⁴⁾	MIL &	\$ L	_	_	1.0 0.2	30 10			
ISB4 Full Standby Current (One Port -	<u>CE</u> "A" < 0.2V and <u>CE</u> "B" > VCC - 0.2V ⁽⁵⁾	COM'L	S L	140 120	190 170	140 120	190 170			mA	
	ČMOS Level Inputs)	VIN > VCC - 0.2V or VIN < 0.2V Active Port Outputs Open f = finax ⁽³⁾	MIL & IND	S L	_	_	140 120	220 200	120 100	190 170	

2746 tbl 07a

			7133X4 7143X4 Com' 8 Military		X45 1 &	7133X55 7143X55 Com'l, Ind & Military		7133X70/90 7143X70/90 Com'l & Military			
Symbol	Parameter	Test Condition	Versio	on	Тур.(1)	Max.	Typ. ⁽¹⁾	Max.	Typ. ⁽¹⁾	Max.	Unit
ICC	Dynamic Operating Current	CE = VIL, Outputs Open	COM'L	S L	230 210	290 250	230 210	285 250	230 210	280 250	mA
	(Both Ports Active)										
ISB1	(Both Ports - TTL Level Inputs) f		COM'L	S L	25 25		25 25		25 25		mA
		I = MAX**		S L							
ISB2	(One Port - TTL	f=fMAX ⁽³⁾	COM'L	S L							mΑ
	Level Inputs)	Active Port Outputs Open	MIL & IND	S L	120 100	210 190	120 100	210 190	Com'l & Military Typ. ⁽¹⁾ Max 230 280 250 230 310 280 210 280 25 60 25 66 120 180 160 120 200 100 180 1.0 15 0.2 4 1.0 30 0.2 10		
ISB3	Full Standby Current (Both Ports - CMOS Level Inputs)	Both Ports CEL and CER > Vcc - 0.2V VN > Vcc - 0.2V or	COM'L	S L	1.0 0.2	15 4	1.0 0.2	15 4			mA
	Civios Level Inpuis)	VIN < 0.2V, f = 0 ⁽⁴⁾	MIL & IND	S L	1.0 0.2	30 10	1.0 0.2	30 10		230	
ISB4	(One Port -	<u>CE</u> "A" < 0.2V and <u>CE</u> "B" > VCC - 0.2V ⁽⁵⁾	COM'L	S L	120 100	180 160	120 100	170 150			mA
	CMOS Level Inputs)	$V_N > V_{CC} - 0.2V$ or $V_N < 0.2V$ Active Port Outputs Open $f = f_{MAX}^{(S)}$	MIL & IND	S L	120 100	200 180	120 100	200 180			

NOTES:

- 1. Vcc = 5V, $TA = +25^{\circ}C$ for Typ., and are not production tested. Icccc = 180mA (typ.)
- 2. 'X' in part number indicates power rating (SA or LA)
- 3. At f = fmax, address and control lines (except Output Enable) are cycling at the maximum frequency read cycle of 1/ tnc, and using "AC Test Conditions" of input levels of GND to 3V.
- 4. f = 0 means no address or control lines change. Applies only to inputs at CMOS level standby.
- 5. Port "A" may be either left or right port. Port "B" is the opposite from port "A".
- 6. Industrial temperature: for other speeds, packages and powers contact your sales office.

2746 tbl 07b

Data Retention Characteristics

(LA Version Only) VLC = 0.2V, VHC = VCC - 0.2V

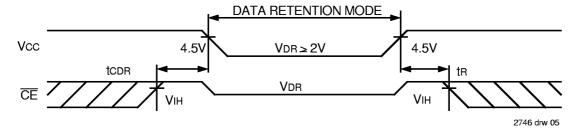
				71			
Symbol	Parameter	Test Condi	tion	Min.	Typ. ⁽¹⁾	Max.	Unit
VDR	Vcc for Data Retention	Vcc = 2V		2.0	1	_	٧
ICCDR	Data Retention Current	CE ≥ Vh c	MIL. & IND.	_	100	4000	μΑ
		Vin ≥ Vhc or ≤ Vlc	COM'L.	_	100	1500	
tcDR ⁽³⁾	Chip Deselect to Data Retention Time			0	1	_	٧
t R ⁽³⁾	Operation Recovery Time			t RC ⁽²⁾		_	V

NOTES:

2746 tbl 08

- 1. Vcc = 2V, TA = +25°C, and are not production tested.
- 2. tRC = Read Cycle Time
- 3. This parameter is guaranteed by device characterization but is not production tested.

Data Retention Waveform



AC Test Conditions

AU 1001 Unitaria	
Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	5ns Max.
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
Output Load	Figures 1, 2 and 3

2746 tbl 09

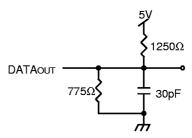


Figure 1. AC Output Test Load

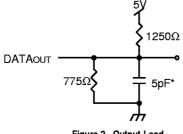


Figure 2. Output Load (for tLz, tHz, twz, tow) *Including scope and jig

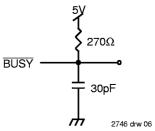


Figure 3. BUSY Output Load (IDT7133 only)

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage (3,4)

		7133X20 7133X25 7143X20 7143X25 Com'l Only Com'l & Military		7133 X 35 7143 X 35 C om'l & Military						
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit		
READ CYCLE	READ CYCLE									
t RC	Read Cycle Time	20	_	25		35	_	ns		
t AA	Address Access Time	_	20		25		35	ns		
t ACE	Chip Enable Access Time	_	20		25		35	ns		
taoe	Output Enable Access Time	_	12	-	15	_	20	ns		
toн	Output Hold from Address Change	0		0		0	_	ns		
t LZ	Output Low-Z Time ^(1,2)	0	_	0		0	_	ns		
tHZ	Output High-Z Time ^(1,2)	_	12	_	15	_	20	ns		
t PU	Chip Enable to Power Up Time ⁽²⁾	0		0		0	_	ns		
t PD	Chip Disable to Power Down Time ⁽²⁾		20		50		50	ns		

2746 tbl 10a

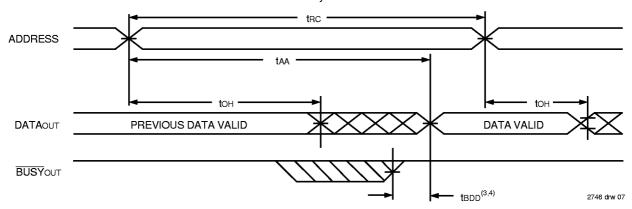
		714 C or	3 X 45 3 X 45 n'l & itar y	7133X55 7143X55 Com'l, Ind & Military		7133X70/90 7143X70/90 Com'l & Military		
Sy mbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
READ CYCLE								
t RC	Read Cycle Time	45		55		70/90	_	ns
t AA	Address Access Time	_	45		55	-	70/90	ns
tACE	Chip Enable Access Time	_	45		55		70/90	ns
taoe	Output Enable Access Time	_	25		30		40/40	ns
tон	Output Hold from Address Change	0		0		0/0	_	ns
t LZ	Output Low-Z Time ^(1,2)	0		5		5/5	_	ns
tHZ	Output High-Z Time ^(1,2)	_	20		20	_	25/25	ns
t PU	Chip Enable to Power Up Time ⁽²⁾	0	_	0		0/0		ns
t PD	Chip Disable to Power Down Time ⁽²⁾	_	50		50		50/50	ns

NOTES:

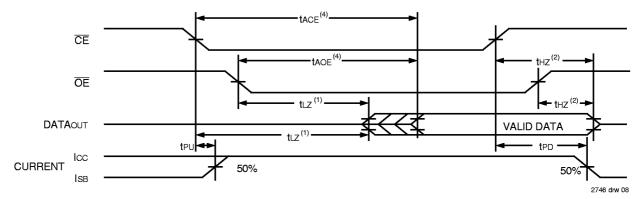
2746 tbl 10b

- 1. Transition is measured ±500mV fromLow or High-impedance voltage with load (Figure 2).
- 2. This parameter is guaranteed by device characterization, but is not production tested.3. 'X' in part number indicates power rating (SA or LA).
- 4. Industrial temperature: for other speeds, packages and powers contact your sales office.

TIMING WAVEFORM OF READ CYCLE NO. 1, EITHER SIDE⁽⁵⁾



TIMING WAVEFORM OF READ CYCLE NO. 2, EITHER SIDE(5)



- 1. Timing depends on which signal is asserted last, $\overline{\text{OE}}$ or $\overline{\text{CE}}$.
- 2. Timing depends on which signal is deasserted first, $\overline{\text{OE}}$ or $\overline{\text{CE}}$.
- 3. tend delay is required only in a case where the opposite port is completing a write operation to the same address location. For simultaneous read operations, BUSY has no relationship to valid output data.
- 4. Start of valid data depends on which timing becomes effective last, tAOE, tACE, tAA, or tBDD.
- RW = V_{IH}, and the address is valid prior to or coincidental with CE transition LOW.

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage (5,6)

		7143	3X20 3X20 I Only	7133X25 7143X25 Com'l & Military		7133X35 7143X35 Com'l & Military		
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
WRITE CYCLE								
twc	Write Cycle Time ⁽³⁾	20	_	25	_	35	_	ns
tew	Chip Enable to End-of-Write	15	_	20	_	25	_	ns
taw	Address Valid to End-of-Write	15	_	20	_	25	_	ns
tas	Address Set-up Time	0	_	0	_	0	_	ns
twp	Write Pulse Width	15	_	20	_	25	_	ns
twr	Write Recovery Time	0	_	0	_	0	_	ns
tow	Data Valid to End-of-Write	15	_	15	_	20	_	ns
tHZ	Output High-Z Time ^(1,2)	_	12	_	15	_	20	ns
toн	Data Hold Time ⁽⁴⁾	0		0		0		ns
twz	Write Enable to Output in High-Z ^(1,2)	_	12	_	15	_	20	ns
tow	Output Active from End-of-Write ^(1,2,4)	0	_	0	_	0	_	ns

2746 tbl 11a

		714: Con	3X45 3X45 1'I & tary	7133X55 7143X55 Com'l, Ind & Military		7133) 7143) Con Mili		
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
WRITE CYCLE								
twc	Write Cycle Time ⁽³⁾	45	_	55	_	70/90	_	ns
tew	Chip Enable to End-of-Write	30	_	40	_	50/50	_	ns
taw	Address Valid to End-of-Write	30	_	40	_	50/50	_	ns
tas	Address Set-up Time	0	_	0	_	0/0	_	ns
twp	Write Pulse Width	30	_	40	_	50/50	_	ns
twr	Write Recovery Time	0	_	0	_	0/0	_	ns
tow	Data Valid to End-of-Write	20	_	25	_	30/30	_	ns
tHZ	Output High-Z Time ^(1,2)	_	20	_	20	_	25/25	ns
toн	Data Hold Time ⁽⁴⁾	5	_	5	_	5/5	_	ns
twz	Write Enable to Output in High-Z ^(1,2)		20	_	20	_	25/25	ns
tow	Output Active from End-of-Write ^(1,2,4)	5	_	5	_	5/5	_	ns

NOTES:

2746 tbl 11b

- Transition is measured ±500mV from Low or High-impedance voltage from the Output Test Load (Figure 2).
 This parameter is guaranteed by device characterization but not production tested.
- 3. For MASTER/SLAVE combination, two = tBAA + twn + twp, since $R\overline{W}$ = VIL must occur after tBAA.
- 4. The specification for tDH must be met by the device supplying write data to the RAM under all operation conditions. Although tDH and tow values will very over voltage and temperature, the actual ton will always be smaller than the actual tow.
- 5. 'X' in part number indicates power rating (SA or LA).
- 6. Industrial temperature: for other speeds, packages and powers contact your sales office.

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage(6,7)

		7133X20 7143X20 Com'l Only		7133X25 7143X25 Com'l & Military		7133X35 7143X35 Com'l & Military		
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
BUSY TIMING	(For MASTER 71V33)							
t BAA	BUSY Access Time from Address		20	_	20		30	ns
t BDA	BUSY Disable Time from Address		20	_	20		30	ns
t BAC	BUSY Access Time from Chip Enable	_	20	_	20		25	ns
t BDC	BUSY Disable Time from Chip Enable		17		20		25	ns
twoo	Write Pulse to Data Delay ⁽¹⁾		40	_	50		60	ns
todo	Write Data Valid to Read Data Delay ⁽¹⁾		30	_	35		45	ns
t BDD	BUSY Disable to Valid Data ⁽²⁾		25	_	30		35	ns
taps	Arbitration Priority Set-up Time ⁽³⁾	5	_	5	_	5	_	ns
twн	Write Hold After BUSY ⁽⁵⁾	20	_	20	_	25	_	ns
BUSY INPUT 1	IMING (For SLAVE 71V43)							
twB	BUSY Input to Write (4)	0	_	0		0	_	ns
twн	Write Hold After BUSY ⁽⁵⁾	20	_	20		25	_	ns
twod	Write Pulse to Data Delay ⁽¹⁾		40	_	50		60	ns
topp	Write Data Valid to Read Data Delay ⁽¹⁾		30		35		45	ns

2746 tbl 12a

		7133X45 7143X45 Com'l & Military		7143 Com	3X55 3X55 I, Ind litary	7133X70/90 7143X70/90 Com'l & Military		
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
BUSY TIMING	(For MASTER 71V33)							
t BAA	BUSY Access Time from Address	_	40	1	40		45/45	ns
t BDA	BUSY Disable Time from Address		40	1	40		45/45	ns
t BAC	BUSY Access Time from Chip Enable	_	30	_	35		35/35	ns
t BDC	BUSY Disable Time from Chip Enable		25	_	30		30/30	ns
twoo	Write Pulse to Data Delay ⁽¹⁾	_	80	_	80		90/90	ns
tooo	Write Data Valid to Read Data Delay ⁽¹⁾	_	55	_	55		70/70	ns
t BDD	BUSY Disable to Valid Data ⁽²⁾	_	40	_	40	_	40/40	ns
taps	Arbitration Priority Set-up Time ⁽³⁾	5	_	5		5/5	_	ns
twн	Write Hold After BUSY ⁽⁵⁾	30	_	30		30/30	_	ns
BUSY INPUT T	IMING (For SLAVE 71V43)							
twB	BUSY Input to Write ⁽⁴⁾	0		0		0/0	_	ns
twн	Write Hold After BUSY ⁽⁵⁾	30	_	30	_	30/30	_	ns
twod	Write Pulse to Data Delay ⁽¹⁾	_	80	ı	80		90/90	ns
tooo	Write Data Valid to Read Data Delay ⁽¹⁾		55		55		70/70	ns

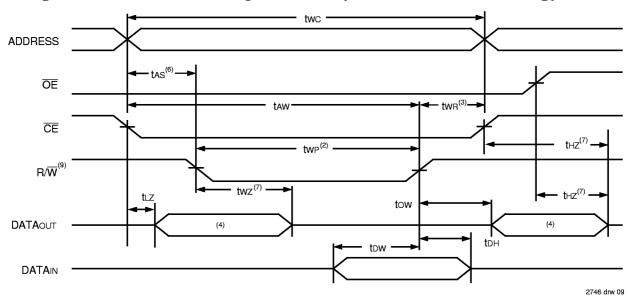
NOTES:

2746 tbl 12b

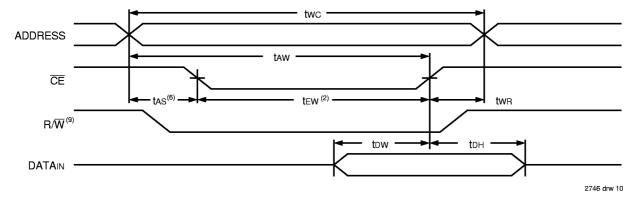
- 1. Port-to-port delay through RAM cells from writing port to reading port, refer to "Timing Waveform of Write with Port-to-Port Read and Busy".
- tbdb is calculated parameter and is greater of 0, twob twp (actual) or tbbb tbw (actual).
- To ensure that the earlier of the two ports wins.
- To ensure that the write cycle is inhibited on port "B" during contention on port "A".

- To ensure that a write cycle is completed on port "B" after contention on port "A".
 To ensure that a write cycle is completed on port "B" after contention on port "A".
 Industrial temperature: for other speeds, packages and powers contact your sales office.

Timing Waveform of Write Cycle No. 1 (R/W Controlled Timing)(1,5,8)

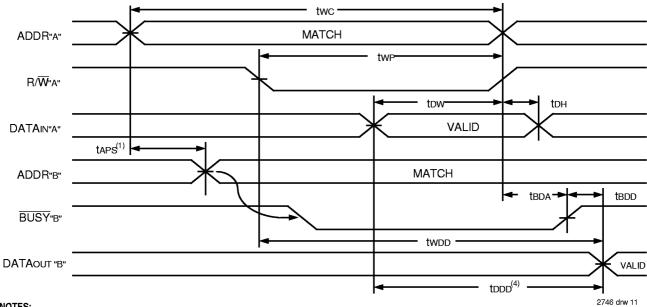


Write Cycle No. 2 (CE Controlled Timing)(1,5)



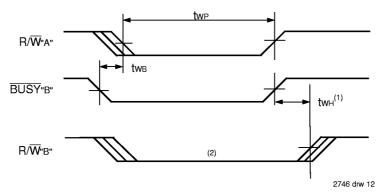
- 1. R/W or CE must be HIGH during all address transitions.
- 2. A write occurs during the overlap (tew or twp) of a \overline{CE} = VIL and a R/ \overline{W} = VIL.
- 3. twn is measured from the earlier of $\overline{\mathbb{CE}}$ or $R\overline{W}$ going HIGH to the end of the write cycle.
- 4. During this period, the I/O pins are in the output state, and input signals must not be applied.
- 5. If the CE LOW transition occurs simultaneously with or after the RW LOW transition, the outputs remain in the High-impedance state.
- 6. Timing depends on which enable signal (\overline{CE} or R/\overline{W}) is asserted last.
- 7. Timing depends on which enable signal is de-asserted first, \overline{CE} or \overline{OE} .
- 8. If \overline{OE} is LOW during a RW controlled write cycle, the write pulse width must be the larger of two or (twz + tow) to allow the I/O drivers to turn off and data to be placed on the bus for the required tow. If \overline{OE} is HIGH during an RW controlled write cycle, this requirement does not apply and the write pulse can be as short as the specified two.
- 9. R/\overline{W} for either upper or lower byte.

Timing Waveform of Write with Port-to-Port Read and BUSY (1,2,3)



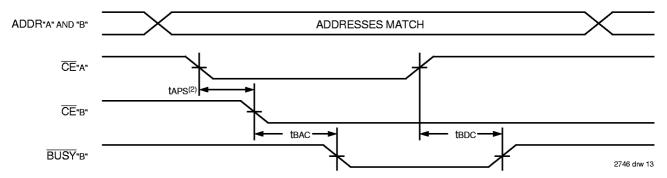
- 1. To ensure that the earlier of the two ports wins, taps is ignored for Slave (IDT7143).
- 2. $\overline{CE}L = \overline{CE}R = VIL$
- 3. $\overline{OE} = V_{IL}$ for the reading port.
- 4. All timing is the same for left and right ports. Port "A" may be either the left or right port. Port "B" is the port opposite from port "A".

Timing Waveform of Write with BUSY⁽³⁾

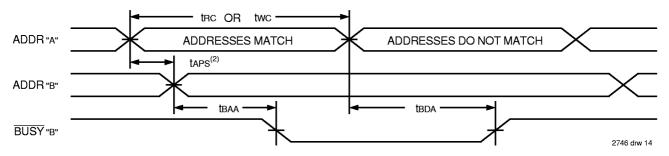


- 1. twn must be met for both BUSY input (IDT7143, slave) and output (IDT7133, master).
- 2. BUSY is asserted on port "B" blocking R/W'B', until BUSY'B' goes HIGH.
- 3. All timing is the same for left and right ports. Port "A" may be either left or right port. Port "B" is the opposite from port "A".

Timing Waveform of BUSY Arbitration Controlled by CE Timing⁽¹⁾



Timing Waveform of BUSY Arbitration Controlled by Addresses⁽¹⁾



- 1. All timing is the same for left and right ports. Port "A" may be either the left or right port. Port "B" is the port opposite from port "A".
- 2. If taps is not satisfied, the BUSY will be asserted on one side or the other, but there is no guarantee on which side BUSY will be asserted (IDT7133 only).

Functional Description

The IDT7133/43 provides two ports with separate control, address and I/O pins that permit independent access for reads or writes to any location in memory. The IDT7133/43 has an automatic power down feature controlled by $\overline{\text{CE}}$. The $\overline{\text{CE}}$ controls on-chip power down circuitry that permits the respective port to go into a standby mode when not selected ($\overline{\text{CE}}$ HIGH). When a port is enabled, access to the entire memory array is permitted. Non-contention READ/WRITE conditions are illustrated in Truth Table 1.

Busy Logic

Busy Logic provides a hardware indication that both ports of the RAM have accessed the same location at the same time. It also allows one of the two accesses to proceed and signals the other side that the RAM is "busy". The BUSY pin can then be used to stall the access until the operation on the other side is completed. If a write operation has been attempted from the side that receives a BUSY indication, the write signal is gated internally to prevent the write from proceeding.

The use of BUSY logic is not required or desirable for all applications. In some cases it may be useful to logically OR the BUSY outputs together and use any BUSY indication as an interrupt source to flag the event of an illegal or illogical operation. If the write inhibit function of BUSY logic is not desirable, the BUSY logic can be disabled by using the IDT7143 (SLAVE). In the IDT7143, the BUSY pin operates solely as a write inhibit input pin. Normal operation can be programmed by tying the BUSY pins HIGH. If desired, unintended write operations can be prevented to a port by tying the BUSY pin for that port LOW. The BUSY outputs on the IDT 7133 RAM are open drain and require pullup resistors.

Width Expansion with Busy Logic Master/Slave Arrays

When expanding an IDT7133/43 RAM array in width while using $\overline{\text{BUSY}}$ logic, one master part is used to decide which side of the RAM array will receive a $\overline{\text{BUSY}}$ indication, and to output that indication. Any number of slaves to be addressed in the same address range as the master, use the $\overline{\text{BUSY}}$ signal as a write inhibit signal. Thus on the IDT7133 RAM the $\overline{\text{BUSY}}$ pin is an output and on the IDT7143 RAM, the $\overline{\text{BUSY}}$ pin is an input (see Figure 3).

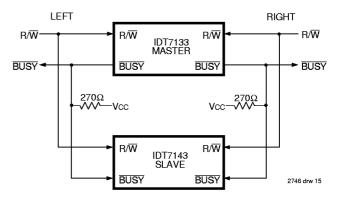


Figure 4. Busy and chip enable routing for both width and depth expansion with the IDT7133 (MASTER) and the IDT7143 (SLAVE).

Expanding the data bus width to 32 bits or more in a Dual-Port RAM system implies that several chips will be active at the same time. If each chip includes a hardware arbitrator, and the addresses for each chip arrive at the same time, it is possible that one will activate its $\overline{\text{BUSYL}}$ while another activates its $\overline{\text{BUSYR}}$ signal. Both sides are now $\overline{\text{BUSY}}$ and the CPUs will await indefinitely for their port to become free.

To avoid the "Busy Lock-Out" problem, IDT has developed a MASTER/SLAVE approach where only one hardware arbitrator, in the MASTER, is used. The SLAVE has $\overline{\text{BUSY}}$ inputs which allow an interface to the MASTER with no external components and with a speed advantage over other systems.

When expanding Dual-Port RAMs in width, the writing of the SLAVE RAMs must be delayed until after the \overline{BUSY} input has settled. Otherwise, the SLAVE chip may begin a write cycle during a contention situation. Conversely, the write pulse must extend a hold time past \overline{BUSY} to ensure that a write cycle takes place after the contention is resolved. This timing is inherent in all Dual-Port memory systems where more than one chip is active at the same time.

The write pulse to the SLAVE should be delayed by the maximum arbitration time of the MASTER. If, then, a contention occurs, the write to the SLAVE will be inhibited due to BUSY from the MASTER.

Truth Table I – Non-Contention Read/Write Control⁽⁴⁾

		LEFT OF	RIGHT PO	PRT ⁽¹⁾		
R/ W LB	R/ W ∪B	CE	Œ	I/O ₀₋₇	I/O8-15	Function
Х	Х	Η	Х	Z	Z	Port Disabled and in Power Down Mode, ISB2, ISB4
Х	Х	Η	Х	Z	Z	CER = CEL = VH, Power Down Mode, ISB1 or ISB3
L	Г	L	Х	DATAIN	DATAIN	Data on Lower Byte and Upper Byte Written into Memory ⁽²⁾
L	н	L	L	DATAIN	DATAout	Data on Lower Byte Written into Memory ⁽²⁾ , Data in Memory Output on Upper Byte ⁽³⁾
Н	L	L	L	DATAout	DATAIN	Data in Memory Output on Lower Byte ⁽³⁾ , Data on Upper Byte Written into Memory ⁽²⁾
L	Н	L	Н	DATAIN	Z	Data on Lower Byte Written into Memory ⁽²⁾
Н	L	L	Н	Z	DATAIN	Data on Upper Byte Written into Memory ⁽²⁾
Н	Н	L	L	DATAout	DATAout	Data in Memory Output on Lower Byte and Upper Byte
Н	Н	L	Н	Z	Z	High Impedance Outputs

NOTES: 2746 tol 13

- 1. AoL A10L≠AoR A10R
- 2. If $\overline{BUSY} = LOW$, data is not written.
- 3. If BUSY = LOW, data may not be valid, see twop and topp timing.
- 4. "H" = HIGH, "L" = LOW, "X" = Don't Care, "Z" = High-Impedance, "LB" = Lower Byte, "UB" = Upper Byte

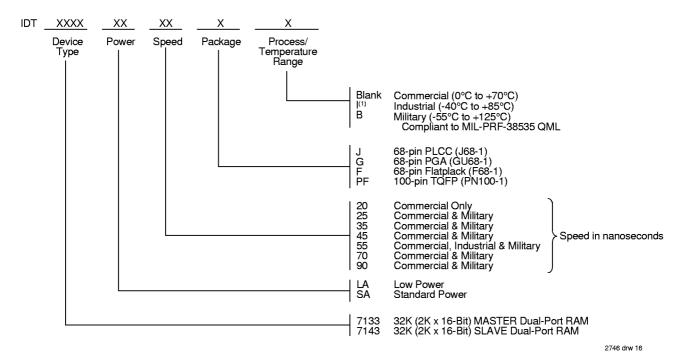
Truth Table II — Address BUSY Arbitration

	In	puts	Out	puts	
CEL	CER	Aol-A1ol Aor-A1or	BUSY _L (1)	BUSYR ⁽¹⁾	Function
Х	Х	NO MATCH	Н	Н	Normal
Н	Х	MATCH	Н	Н	Normal
Х	Н	MATCH	Н	Н	Normal
L	L	MATCH	(2)	(2)	Write Inhibit ⁽³⁾

-a 27-

- Pins BUSYL and BUSYR are both outputs on the IDT7133 (MASTER). Both are inputs on the IDT7143 (SLAVE). On Slaves the BUSY input internally inhibits writes.
- "L" if the inputs to the opposite port were stable prior to the address and enable
 inputs of this port. "H" if the inputs to the opposite port became stable after the
 address and enable inputs of this port. If taps is not met, either BUSYL or BUSYR
 = VIL will result BUSYL and BUSYR outputs can not be LOW simultaneously.
- Writes to the left port are internally ignored when BUSYL outputs are driving LOW regardless of actual logic level on the pin. Writes to the right port are internally ignored when BUSYR outputs are driving LOW regardless of actual logic level on the pin.

Ordering Information



NOTE:

1. Industrial temperature range is available on selected PLCC packages in standard power. For other speeds, packages and powers contact your sales office.

Datasheet Document History

Initiated datasheet document history 12/18/98:

Converted to new format

Cosmetic and typographical corrections Added additional notes to pin configurations

Page 2 corrected PN100 pinout

2/17/99: Corrected PF ordering code

3/9/99: Cosmetic and typographical corrections



CORPORATE HEADQUARTERS

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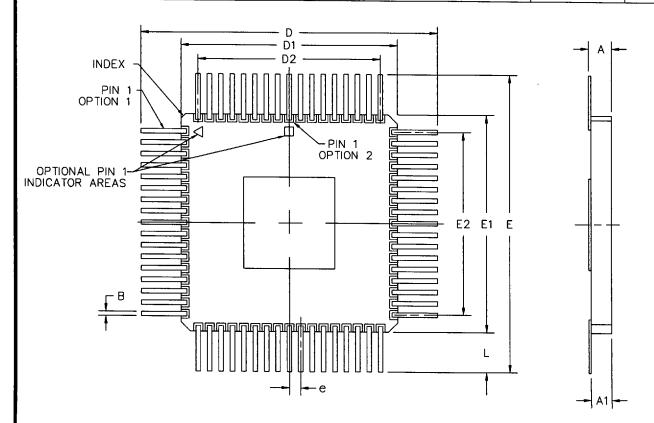
for Tech Support:

831-754-4613

DualPortHelp@idt.com

FLATPACK (Continued)

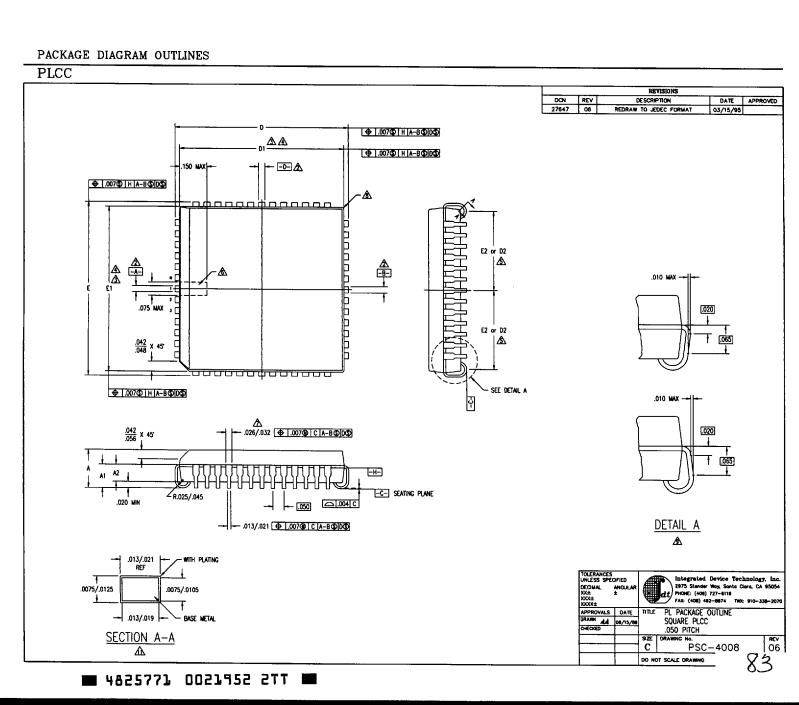
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17049	00	ORIGINAL ISSUE	11/30/89	D. G.
19350	01	CHANGE PIN 1 LOCATION	11/07/90	D. G.
27425	02	CHANGE PIN 1 LOCATION	01/05/95	D. D.
28663	03	ADDED PIN 1 OPTION 2		



NOTES: (UNLESS OTHERWISE SPECIFIED)

- 1. ALL DIMENSIONS ARE IN INCHES.
- 2. BSC BASIC LEAD SPACING BETWEEN CENTERS.
- 3. SYMBOL "N" REPRESENTS NUMBER OF LEADS.
- 4. INDEX CHAMFER .020, OTHER CHAMFERS .040 (X3).

					CON	IFIGUR.	ATION	E	KCEPTION	1S
DWG #	F68	-1	JEDEC	2	MO-081-AA			NONE		
SYMBOL	MIN	MAX	MIL-M-3	8510	N	NOT LISTED			N/A	
Α	.080	.145	TOLERANCES L			Into	arated D	orrigo '	Toob wel	
A1	.070	.090	OTHERWISE SPE FRAC DEC A			\	grated D			
В	.016	.021] ± - ± -	± -		1 + 1	36 Scott Blv			
С	.008	.012	APPROVALS	DATE		(40)	8) 727–6116	FAX:	(408) 7	27-2328
D/E	1.640	1.870								
D1/E1	.926	.970	DRAWN A.A	11/89	168 I		UAD	-ι Δ ٦	PA	^k
D2/E2	.800	BSC	CHECKED							
е	.050	BSC			MARK	(EII	ng df	4AMI	NG	
L	.350	.450			SCALE	SIZE	DRAWING NO			REV
Ν	6	8		-	NI / A				05	
ND	1	7		<u> </u>	IN/A	A	PSC	-20	<u>100</u>	03
					DO NOT SCALE DRAWING			1	SHEET	11



PACKAGE DIAGRAM OUTLINES

PLCC (Continued)

		REVISIONS		
DCN	REV	DESCRIPTION	DATE	APPROVED
27647	06	REDRAW TO JEDEC FORMAT	03/15/95	

	DWG #		J28-	1	DWG	1	J44-	1	DWG	1	J52-	1	DWG	#	J68-	1	DWG	#	J84-	1
Ş	JEDE	C VARIAT	ION	N	JEDE	C VARIAT	ION	N	JEDE	C VARIAT	ION	N	JEDE	C VARIAT	10N	N	JEDEC VARIATION			
9		AB] 🖁		AC] P		AD		🖁		AE		P		AF		ļĝ
Ľ	MIN	NOM	MAX	E	MIN	NOM	MAX	É	MIN	NOM	MAX	Ė	MIN	NOM	MAX	È	MIN	NOM	MAX	Ė
A	.165	.172	.180		.165	.172	.180		.165	.172	.180		.165	.172	.180		.165	.172	.180	
A1	.095	.105	.115		.095	.105	.115		.095	.105	.115		.095	.105	.115		.095	.105	.115	_
A2	.062	_	.083		.062	-	.083		.062	T -	.083		.062	-	.083	М	.059	-	.080	\vdash
D	.485	.490	.495		.685	.690	.695		.785	.790	.795		.985	.990	.995		1.185	1,190	1.195	
D1	.450	.453	.456	3,4	.650	.653	.656	3,4	.750	.753	.756	3,4	.950	.953	.956	3.4	1,150	1.154	1,156	3.4
D2	.195	.205	.215	5	.295	.305	.315	5	.345	.355	.365	5	.445	.455	.465	5	.545	.555	.565	5
Ε	.485	.490	.495		.685	.690	.695		.785	.790	.795		.985	.990	.995		1.185	1,190	1,195	- <u>-</u>
E١	.450	.453	.456	3,4	.650	.653	656	3,4	.750	.753	.756	3,4	.950	953	.956	3,4	1,150	1.154	1.156	3,4
E2	.191	.205	.219	5	.291	.305	.319	5	.341	.355	.369	5	.441	.455	.469	5	.541	.555	.569	5
N		28				44			1	52				68				84		Ť

NOTES:

1 ALL DIMENSIONING AND TOLERANCING CONFORM TO ANSI Y14.5M-1982

DATUMS A-B AND -D- TO BE DETERMINED AT DATUM PLANE -H-

⚠ DIMENSIONS D1 AND E1 ARE TO BE DETERMINED AT DATUM PLANE —H—

⚠ DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD PROTRUSION. ALLOWABLE MOLD PROTRUSION IS .010 PER SIDE. D1 AND E1 ARE BODY SIZE DIMENSIONS INCLUDING MOLD MISMATCH

△ DIMENSIONS D2 AND E2 ARE TO BE DETERMINED AT SEATING PLANE —C—CONTACT POINT

DETAIL OF PIN 1 IDENTIFIER IS OPTIONAL BUT MUST BE LOCATED WITHIN THE ZONE INDICATED

LEAD WIDTH DIMENSION DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION IS .007 TOTAL MAXIMUM PER LEAD

A EXACT SHAPE OF EACH CORNER IS OPTIONAL

10 ALL DIMENSIONS ARE IN INCHES

 Φ

THIS OUTLINE CONFORMS TO JEDEC PUBLICATION 95 REGISTRATION MS-018, VARIATION AB, AC, AD, AE & AF. EXCEPTIONS: JEDEC MAXIMUM BASE METAL LEAD WIDTH IS .018

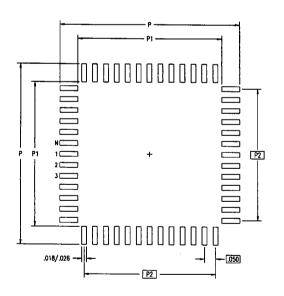
TOLERANCES UNLESS SPEI DECIMAL XX± XXX± XXXX±		Integrated Device Technology, Inc. 2975 Stender Woy, Sente Clere, CA 95034 PHONE: (408) 727-8118 FAX: (408) 492-8674 TRX: 910-338-2070							
APPROVALS	DATE	TITLE	PL PACKAGE OUTLI	NE					
DRAWN ALA	08/15/86	1	SQUARE PLCC						
CHECKED		1	.050 PITCH						
		SIZE	DRAWING No.		REV				
		С	PSC-40	800	06				
		DO NO	T SCALE DRAWING	01	1				
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PACKAGE DIAGRAM OUTLINES

PLCC (Continued)

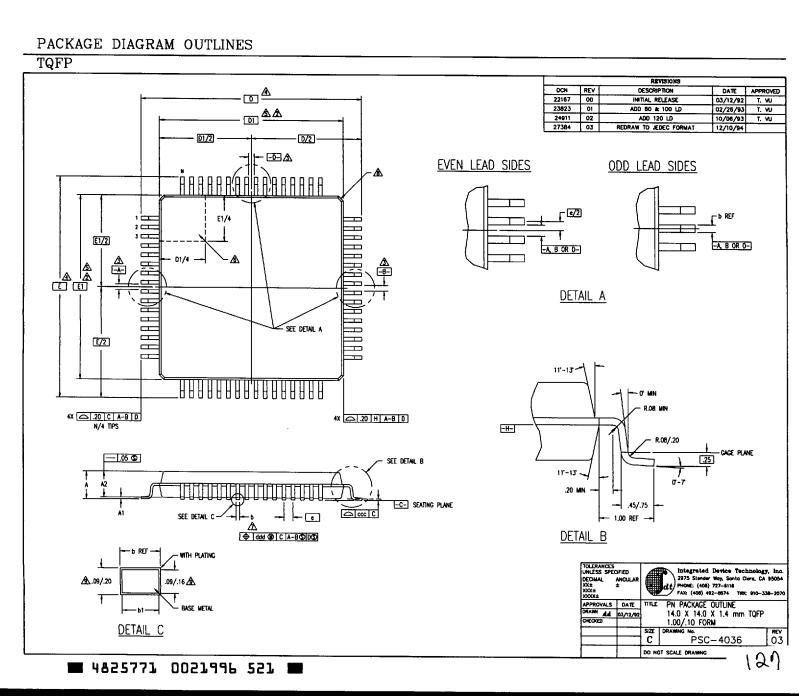
REVISIONS												
DCN	Æ	DESCRIPTION	DATE	APPROVED								
27647	8	REDRAW TO JEDEC FORMAT	03/15/95									

LAND PATTERN DIMENSIONS



	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX		
P	.520	.528	.720	.728	.820	.828	1.020	1.028	1.220	1.228		
P1	.354	.362	.554	.562	.654	.662	.854	.862	1.054	1.062		
P2	.300 BSC .50		.500	BSC	.600	BSC	.800	BSC	1.000	BSC		
N	28			14	52		52		6	8	8	4

TOLERANCES UNLESS SPE DECIMAL XX± XXX± XXXX± XXXX±			Integrated Device Technolog 2975 Stender Woy, Sonto Clora, CA PHONE: (408) 727-8116 FAX: (408) 482-8674 TWX: 910-3	95054
APPROVALS	DATE	TITLE	PL PACKAGE OUTLINE	
DRAWN ALL	08/15/89		SQUARE PLCC	
CHECKED		ŀ	.050 PITCH	
		SZE	DRAWING No.	REV
		С	PSC-4008	06
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PACKAGE DIAGRAM OUTLINES

TQFP (Continued)

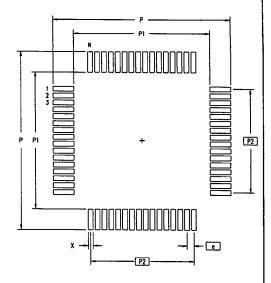
			PN64-1 DWG		; 	PN80	PN80-1		31	PN10	0-1	DWG #		PN120-1		
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Ĉ	MIN	NOM	MAX	E	MIN	NOM	MAX	Ė	MIN	NOM	MAX] Ė	MIN	NOM	MAX	Ė
Α	-		1.60		_	-	1.60		-	-	1.60		_	-	1.60	
A1	.05	.10	.15		.05	.10	.15		.05	.10	.15	\Box	.05	.10	.15	
A2	1.35	1.40	1.45		1.35	1.40	1.45		1.35	1.40	1.45	\Box	1.35	1.40	1.45	\sqcap
0		16.00 BSC 4 16.00 BSC				4	16.00 BSC 4		4	16.00 BSC		4				
D1	1	14.00 BSC 5,2 14.00 BSC				5,2	14.00 BSC 5,2		5,2	14.00 BSC			5,2			
E	1	6.00 BS	C	4	1	6.00 85	С	4		6.00 BS	c	4	1	6.00 BS	C	4
Εĩ	.1	4.00 BS	C	5,2	1	4.00 BS	С	5,2	14.00 BSC			5,2	14.00 BSC		С	5,2
N		64				80			100			П	120			Ħ
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Ь	.30	.37	.45	7	.22	.32	.38	7	.17	.22	.27	7	.13	.18	.23	7
ь١	.30	.35	.40		.22	.30	.33		.17	.20	.23		.13	.16	.19	1
ccc	-	-	.10		-	_	.10		-	-	.08	\Box		-	.08	
ddd	-	_	.20		-	-	.13		-	-	.08		-	-	.07	

NOTES:

- 1 ALL DIMENSIONING AND TOLERANCING CONFORM TO ANSI Y14.5M-1982
- TOP PACKAGE MAY BE SMALLER THAN BOTTOM PACKAGE BY .15 mm
- ⚠ DATUMS A-B AND -D- TO BE DETERMINED AT DATUM PLANE -H-
- Δ DIMENSIONS D AND ε ARE TO BE DETERMINED AT SEATING PLANE —C-
- DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD PROTRUSION. ALLOWABLE MOLD PROTRUSION IS .25 mm PER SIDE. D1 AND E1 ARE MAXIMUM BODY SIZE DIMENSIONS INCLUDING MOLD MISMATCH
- DETAILS OF PIN 1 IDENTIFIER IS OPTIONAL BUT MUST BE LOCATED WITHIN THE ZONE INDICATED
- DIMENSION 6 DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION IS .08 mm in excess of the 6 dimension at maximum material condition. Dambar cannot be located on the lower radius or the foot.
- A EXACT SHAPE OF EACH CORNER IS OPTIONAL
- THESE DIMENSIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN .10 AND .25 mm FROM THE LEAD TIP
- 10 ALL DIMENSIONS ARE IN MILLIMETERS
- 11 This outline conforms to jedec publication 95 registration Mo-136, variation 8P, 8Q, 8R & 8S

	REVISIONS										
DCN	REV	DESCRIPTION	DATE	APPROVED							
22167	00	INITIAL RELEASE	03/12/92	T. W							
23823	01	ADD 80 & 100 LD	02/26/93	T. VU							
24911	02	ADD 120 LD	10/06/93	T. VU							
27384	03	REDRAW TO JEDEC FORMAT	11/18/94								

LAND PATTERN DIMENSIONS



	MIN	MAX	MRN	MAX	MIN	MAX	MIN	MAX	
Ρ	16.80	17.00	16.80	17.00	16.80	17.00	16.80	17.00	
P1	13.80	14.00	13.80	14.00	13.80	14.00	13.80	14.00	
P2	12.00	BSC	12.35	BSC	12.00 BSC		11.60 BSC		
Χ	.40	.60	.30	.50	.30	40	.20	.30	
e	.80 BSC		.65 BSC		.50 BSC		.40 BSC		
N	6	4	80		100		120		

TOLERANCES UNLESS SPE DECIMAL XX± XXX± XXXX±			Integrated Device Technolog 2975 Stender Way, Santa Clora, CA PHONE: (408) 727-8116 FAX: (408) 482-8874 TWX: 910-33	95054
APPROVALS	DATE	TITLE	PN PACKAGE OUTLINE	
DRAWN ALA	03/12/92	1	14.0 X 14.0 X 1.4 mm TQFP	
CHECKED	1	1	1.0D/.10 FORM	
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		С	PSC-4036	03
		DO N	OT SCALE DRAWING	<u>()</u>
			la	8

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